

**AMENDMENTS TO THE SPECIFICATION**

**IN THE SPECIFICATION:**

Please amend the paragraph starting at page 10, line 14, as follows:

To be more specific, the GaAs layer 31,  $Al_{0.15}Ga_{0.85}As$  layer 32 and  $Al_{0.3}Ga_{0.7}As$  layer 33 constituting the buffer layer 30 are formed at relatively fast growth rates, and the  $Al_{0.4}Ga_{0.6}As$  layer 41 that is the first first layer of the multilayer structure 4 is formed at a slower growth rate than the growth rate of the buffer layer 3 30.